# 2SK2509

### Silicon N-Channel Power F-MOS

### ■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown

### Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

## ■ Absolute Maximum Ratings (Tc = 25°C)

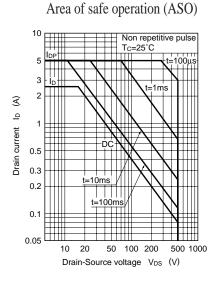
Parameter		Symbol	Rating	Unit	
Drain-Source breakdown voltage		$V_{\rm DSS}$	500	V	
Gate-Source voltage		$V_{GSS}$	±30	V	
Drain current	DC	$I_D$	±2.5	A	
	Pulse	$I_{DP}$	±5	A	
Avalanche energy capability		EAS*	15.6	mJ	
Allowable power dissipation	$T_C = 25^{\circ}C$	D	40	W	
	Ta= 25°C	$P_{D}$	1.3	Wow W	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature		T <sub>stg</sub>	-55 to +150	%C %	

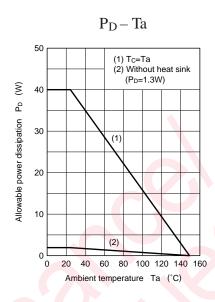
<sup>\*</sup> L= 5mH,  $I_L$ = 2.5A, 1 pulse

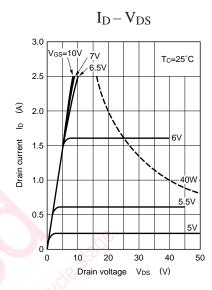
# Unit: mm 3.4±0.3 6.0±0.5 1.5max. 1.1max. 0.5max. 1: Gate 2: Drain 3: Source N Type Package

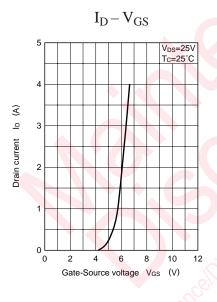
### ■ Electrical Characteristics (Tc = 25°C)

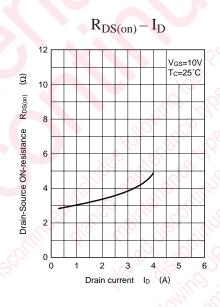
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source cut-off current	-	$V_{DS}$ = 400V, $V_{GS}$ = 0	IVIIII	Тур	100	
	$I_{DSS}$	VDS- 400 V, VGS- 0			100	μΑ
Gate-Source leakage current	I <sub>GSS</sub>	$V_{GS}=\pm30V, V_{DS}=0$			±1	μΑ
Drain-Source breakdown voltage	V <sub>DSS</sub>	$I_D=1$ mA, $V_{GS}=0$	500			V
Gate threshold voltage	V <sub>th</sub>	$V_{DS}=25V$ , $I_D=1mA$	2		5	V
Drain-Source ON-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =1.5A		3.2	4	Ω
Forward transadmittance	Y <sub>fs</sub>	V <sub>DS</sub> = 25V, I <sub>D</sub> =1.5A	1	1.5		S
Diode forward voltage	V <sub>DSF</sub>	$I_{DR} = 2.5A, V_{GS} = 0$			-1.5	V
Input capacitance	C <sub>iss</sub>			330		pF
Output capacitance	Coss	$V_{DS}$ = 20V, $V_{GS}$ = 0, f= 1MHz		55		pF
Feedback capacitance	C <sub>rss</sub>			20		pF
Turn-on time (delay time)	t <sub>d(on)</sub>			15		ns
Rise time	t <sub>r</sub>	V <sub>DD</sub> =150V, I <sub>D</sub> =1.5A		25		ns
Fall time	$t_{\mathrm{f}}$	$V_{GS}=10V, R_L=100\Omega$		30		ns
Turn-off time (delay time)	t <sub>d(off)</sub>			55		ns
Channel-Case heat resistance	R <sub>th(ch-c)</sub>				3.125	°C/W
Channel-Atmosphere heat resistance	R <sub>th(ch-a)</sub>				96.15	°C/W

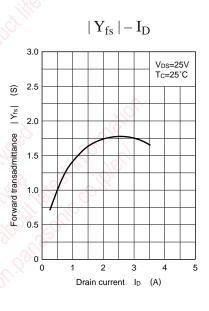


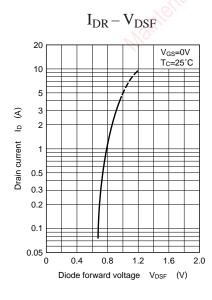


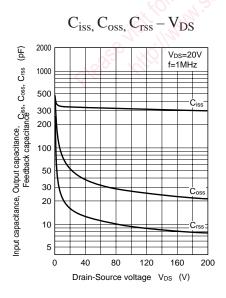


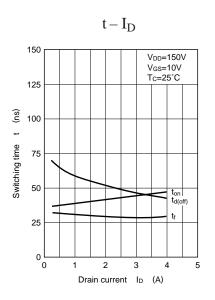




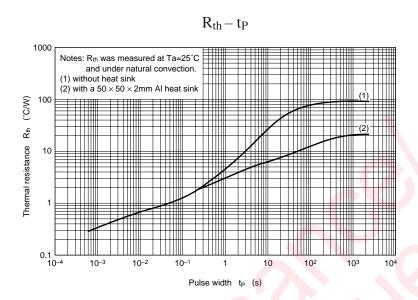








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